

# PSMN1R6-30PL

N-channel 30 V 1.7 mΩ logic level MOSFET

Rev. 02 — 25 June 2009

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference

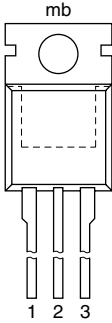
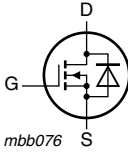
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V	
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a> ;	[1]	-	100	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	306	W	
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 15\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	27	-	nC	
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 15\text{ V};$ see <a href="#">Figure 14</a>	-	101	-	nC	
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$	[2]	-	1.4	1.7	mΩ

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;"><b>SOT78</b> (TO-220AB; SC-46)</p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PSMN1R6-30PL	TO-220AB; SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

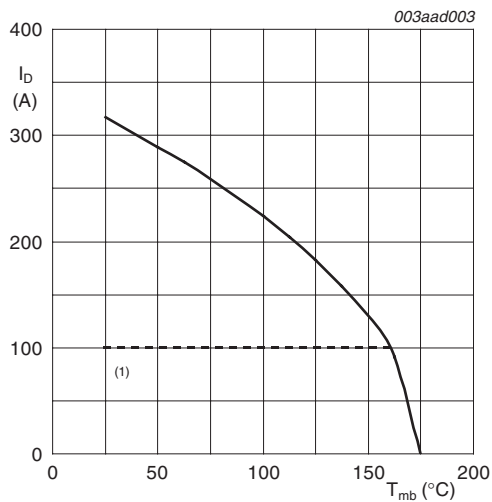
## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a> ;	[1]	100	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a> ;	[1]	100	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	1268	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	306	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$ ;	[1]	100	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	1268	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 100\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped	-	1.7	J

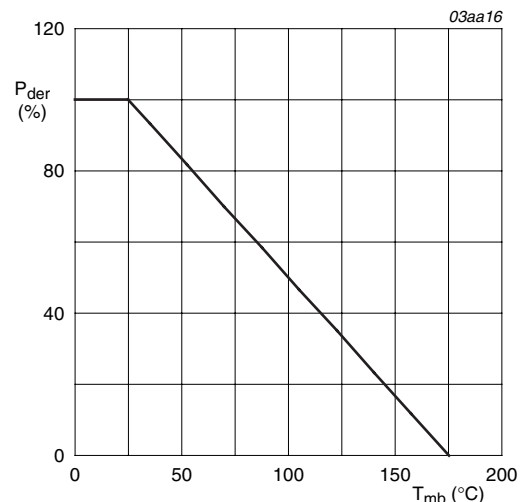
[1] Continuous current is limited by package.



$$V_{GS} \geq 10\text{ V}$$

(1) Capped at 100 A due to package.

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**

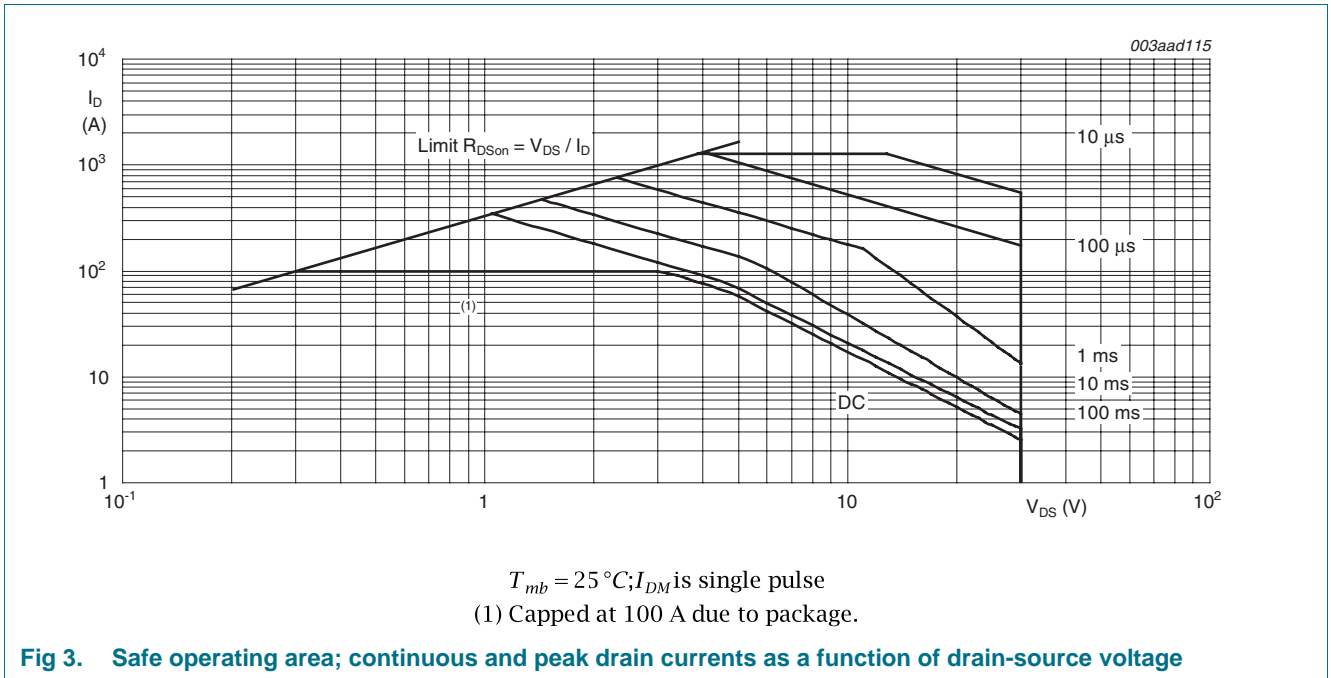


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.22	0.49	K/W

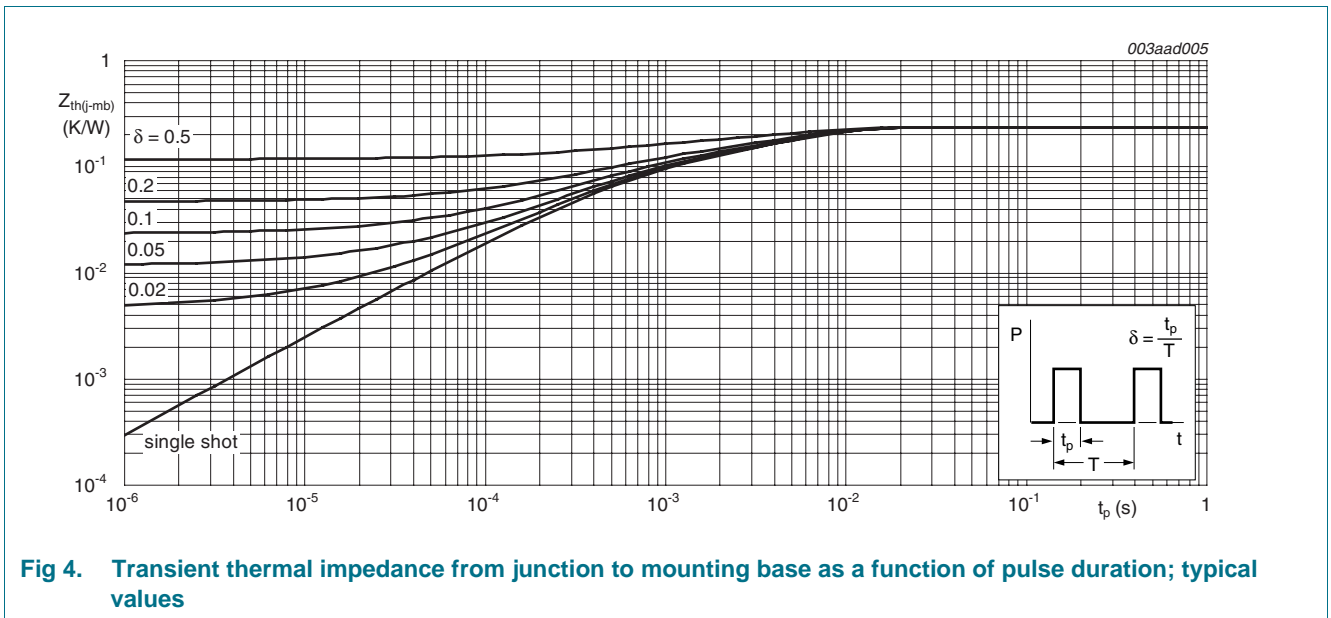


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 6. Characteristics

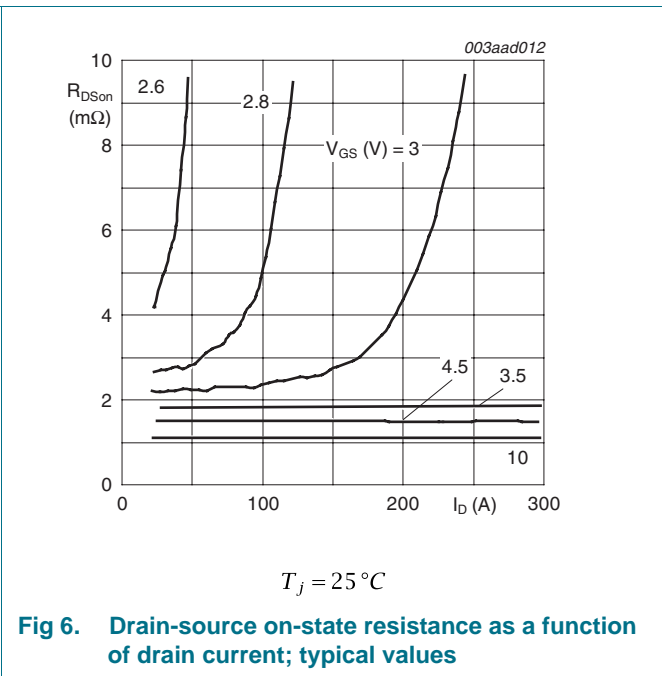
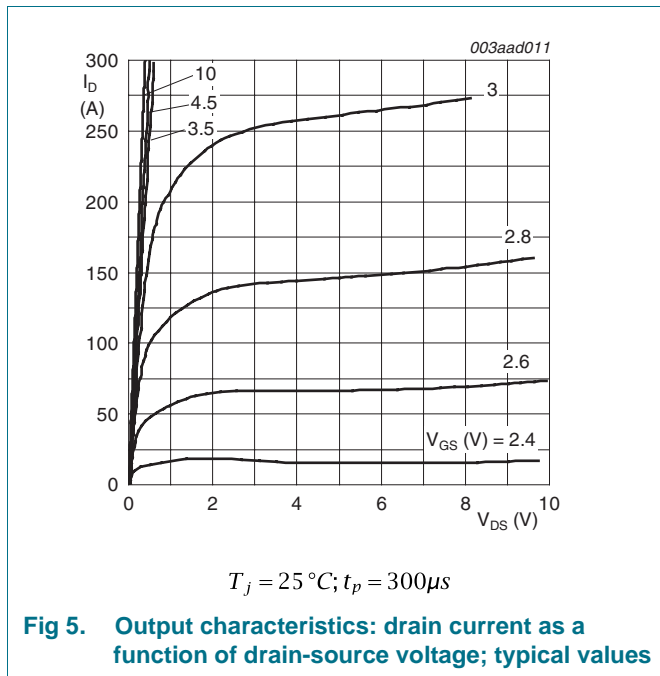
**Table 6. Characteristics**
*Tested to JEDEC standards where applicable.*

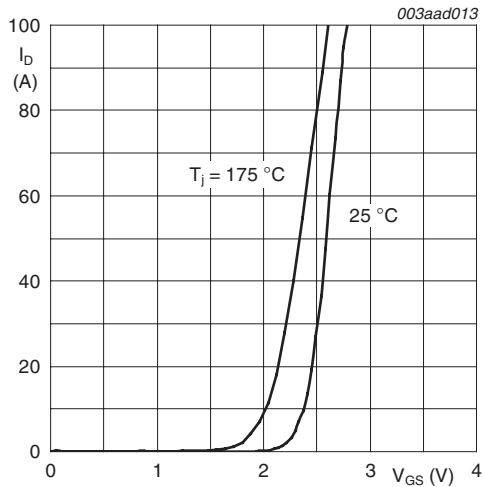
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>	-	-	2.45	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	5	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	150	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	1.6	2.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>	-	-	2.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">[1]</a>	-	1.4	1.7	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	0.98	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	212	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	193	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a>	-	101	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	33	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a>	-	20	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	13	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	27	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 15 \text{ V}$ ; see <a href="#">Figure 14</a>	-	2.5	-	V
$C_{iss}$	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 16</a>	-	12493	-	pF
$C_{oss}$	output capacitance		-	2486	-	pF
$C_{rss}$	reverse transfer capacitance		-	1034	-	pF

**Table 6. Characteristics ...continued**  
 Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}; R_L = 0.5\ \Omega; V_{GS} = 4.5\text{ V};$	-	104	-	ns
$t_r$	rise time	$R_{G(ext)} = 4.7\ \Omega$	-	163	-	ns
$t_{d(off)}$	turn-off delay time		-	174	-	ns
$t_f$	fall time		-	87	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 17</a>	-	0.77	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 50\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	64	-	ns
$Q_r$	recovered charge	$V_{DS} = 15\text{ V}$	-	79	-	nC

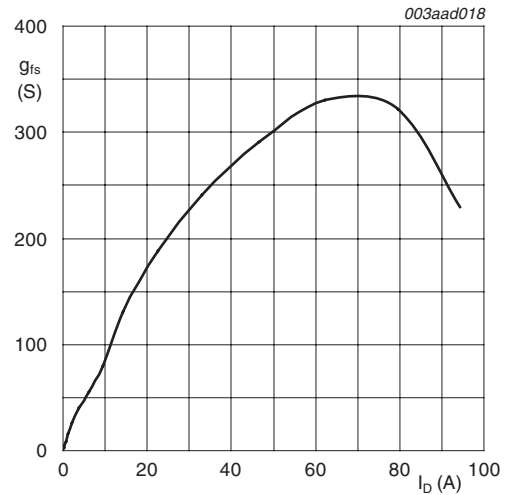
[1] Measured 3 mm from package.





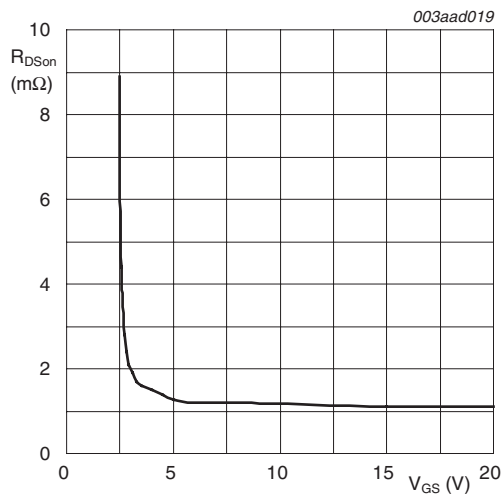
$V_{DS} = 15\text{V}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



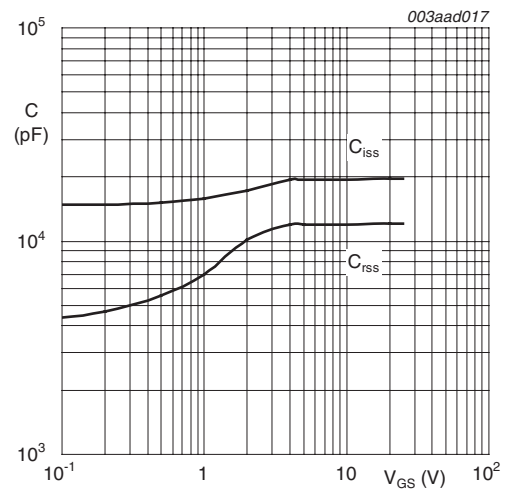
$T_j = 25^\circ\text{C}; V_{DS} = 15\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



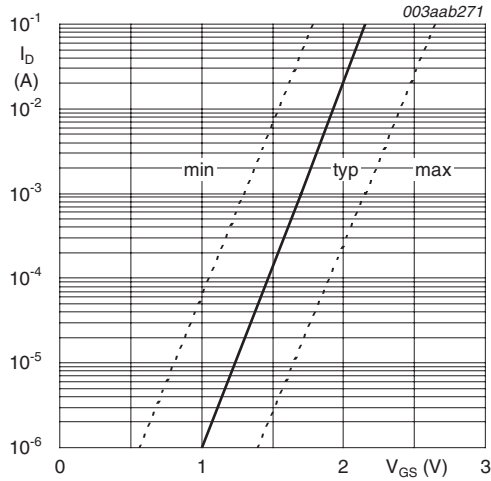
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



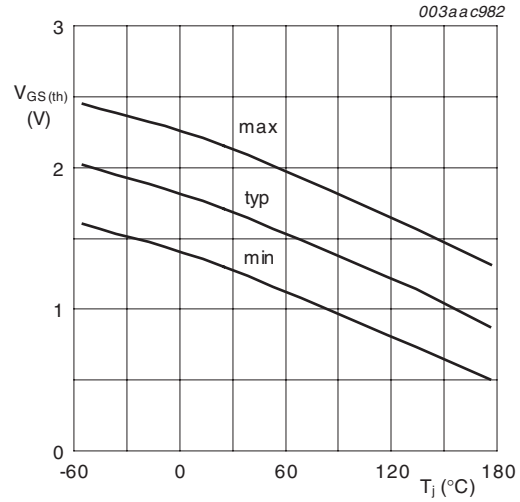
$V_{DS} = 0\text{V}; f = 1\text{MHz}$

Fig 10. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



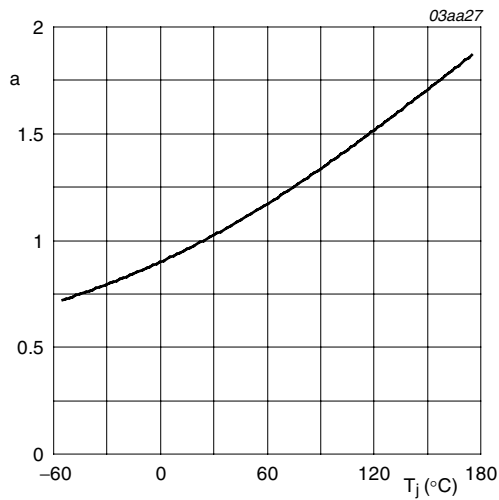
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$I_D = 1\text{mA}; V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

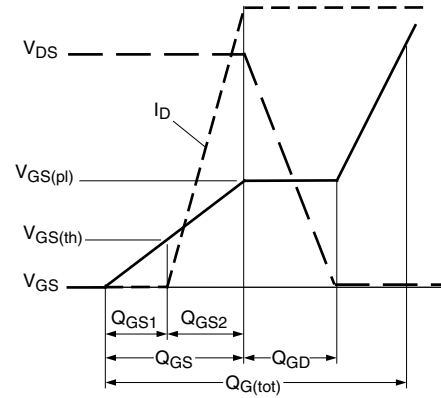
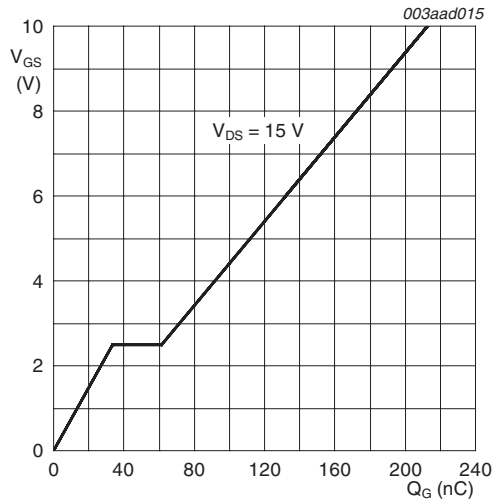


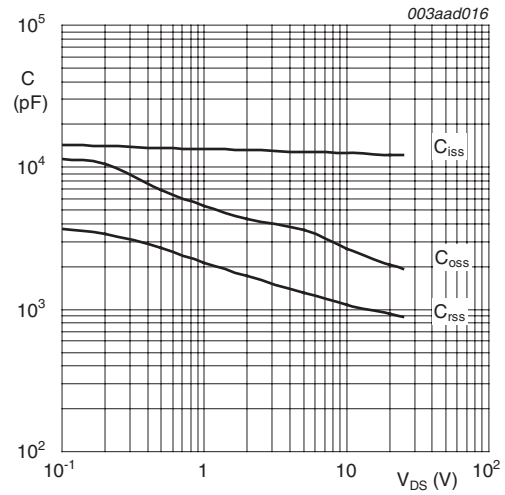
Fig 14. Gate charge waveform definitions





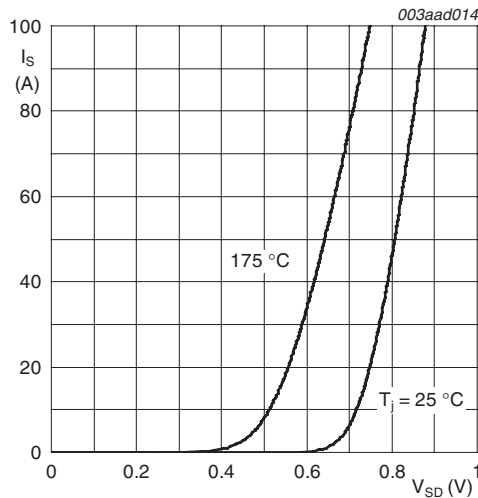
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

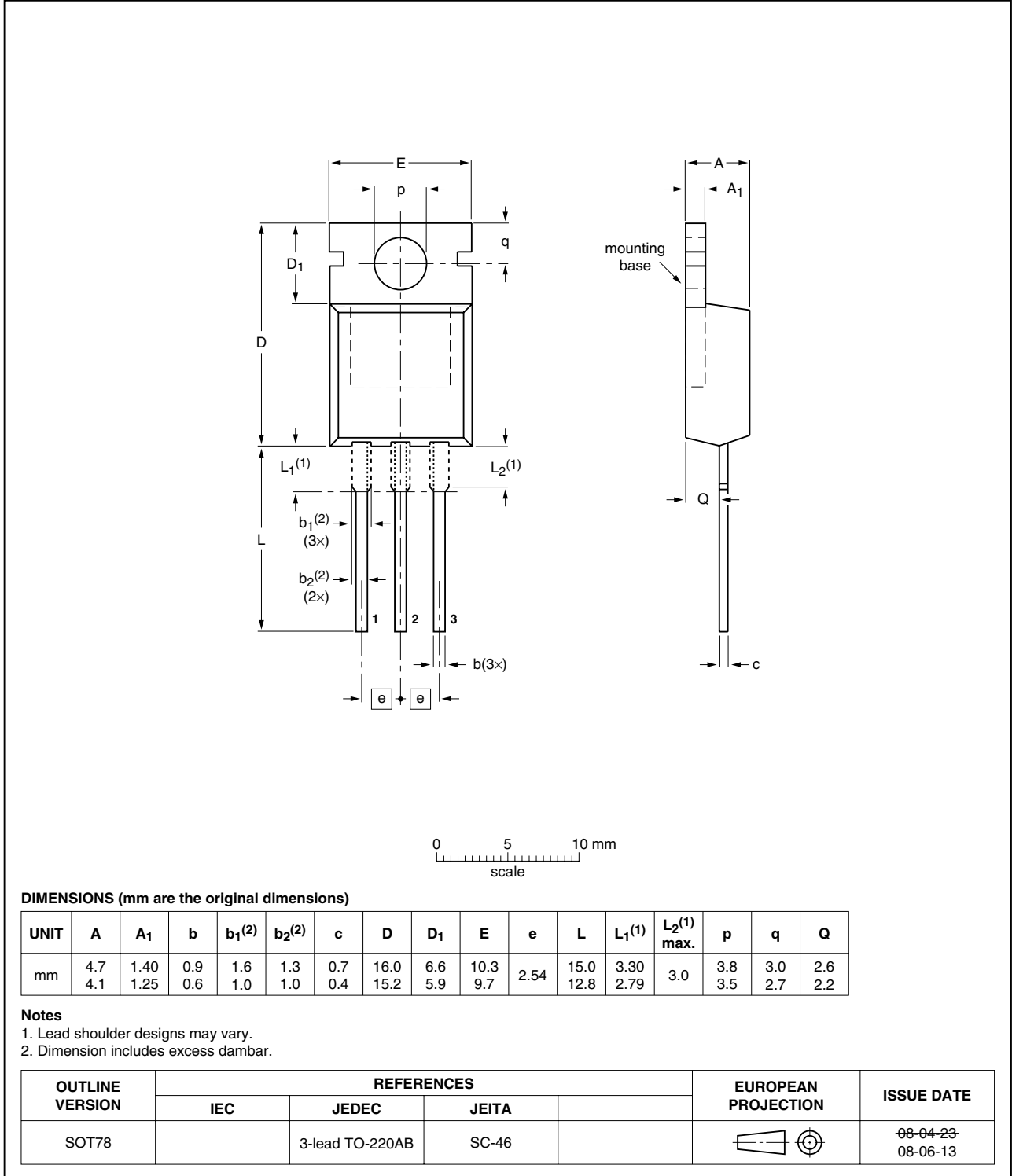


Fig 18. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R6-30PL_2	20090625	Product data sheet	-	PSMN1R6-30PL_1
Modifications:		<ul style="list-style-type: none"><li>• Data sheet status changed from objective to product.</li><li>• Various content changes.</li></ul>		
PSMN1R6-30PL_1	20090518	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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